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Plasmon dispersion in quasi-one and one-dimensional systems with non-magnetic impurities

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We calculate the plasmon dispersion in quasi-one-dimensional quantum wires, in the presence of non-magnetic impurities, taking into consideration the memory function formalism and the role of the forward scattering. The plasma frequency is reduced by the presence of impurities. We also calculate, analytically, the plasmon dispersion in the Born approximation, for the scattering of the electrons by the non-magnetic impurities. We compare our result with the numerical results of Sarma and Hwang.

Keywords: Quasi-one-dimensional systems, Disorder, Forward scattering, Plasmon modes, Memory function formalism, Born approximation

1. Introduction

The problem of the existence of one-dimensional plasmon modes was discussed by Ritsko et.al.[1] after the measurements on one-dimensional organic metals by high-energy inelastic electron scattering in thin crystalline films. Short after, Williams and Bloch [2] developed a random-phase-approximation (RPA) model, in order to calculate the dielectric response of a quasi-one-dimensional metal, with the result in a good agreement with the experimental data. They also predict an acoustic-plasmon branch. The progress in semiconductor fabrication allowed the experimentalists for the realization of systems where electrons are confined in one dimension [3]. The measurements were performed on GaAs quantum wires, using the inelastic resonant light scattering spectroscopy that allow for the investigation of the collective and single-particle excitations of the electron gas. The measured wave-vector dependence of the plasmon dispersion was in qualitative agreement with the random-phase-approximation calculations. Li et.al.[4], showed that the RPA provides an exact description of the plasmon dispersion in one-dimensional wires, by establishing an equivalence between RPA and Tomonaga-Luttinger liquid model [5,6]. The dynamical response of an one-dimensional electron system in a quantum-wire was theoretically and numerically analyzed, within RPA, by Sarma and Hwang

[7]. They also included the effect of disorder, in the Born approximation, using a numerical procedure in order to find the modified plasma frequency. The effect of the electron-electron correlations on the scattering processes in quantum wires was discussed by Thakur and Neilson [8]. The scattering rate increases with the increasing of the electron correlations, and the plasmon dispersion depends on the electron correlations and on the level of disorder. Other measurements, on quasi-one-dimensional organic conductors [9], established the frequency dependence of the conductivity, that can be explained using the role of the forward scattering by impurities [10]. In this paper, we will analyze the plasmon dispersion in quasi-one-dimensional systems in the presence of disorder, beyond the Born approximation, using the memory function formalism. We also calculate, analytically, the plasma frequency in the Born approximation. The similarities and the differences between the models are discussed.

2. Model

In order to calculate the quasi-one-dimensional plasma frequency, we use a model that consists in a quasi-one-dimensional conductor with disorder that can be modelled by the Gaussian potential $V(x)$, with the average $\overline{V}(x) = 0$, and the correlator given by:

$$\overline{V(x)\,V(x')} = \gamma_0\,C(x-x') \tag{1}$$

where γ_0 is a measure of the strength of the disorder, and $C(x)$ is defined in Ref.[10]. The plasmon dispersion will be analyzed investigating the zeros of the complex dielectric function:

$$\epsilon(q,\omega) = 1 - V(q)\,\chi(q,\omega) \tag{2}$$

Here $V(q)$ is the Fourier transform of the Coulomb interaction, and $\chi(q,\omega)$ is the density-density response function. According to Ref.[11], $\chi(q,\omega)$ can be expressed, in the long-wavelength limit, as:

$$\chi(q,\omega) \simeq -\frac{iq^2}{\omega e^2}\,\sigma(\omega) \tag{3}$$

where $\sigma(\omega)$ is the frequency dependent conductivity. In our model we take into consideration the effect of forward scattering by impurities in an interacting electron system. Using the memory function formalism, according to Ref.[12], the frequency dependent conductivity is given by:

$$\sigma(\omega) = \frac{iD_c}{\omega + M(\omega)} \tag{4}$$

Here D_c is the charge stiffness, and $M(\omega)$ is the memory function (which includes the vertex corrections to all orders in the perturbation theory. $M(\omega)$

is expressed in powers of the impurity potential). The memory function will be calculated using the Tomonaga-Luttinger model with interaction parameters $g_2 = g_4 = \pi v_F F$, where v_F is the Fermi velocity, and F is an interaction parameter, and with:

$$\Pi(q,\omega) = Z_q \, \frac{2\omega_q}{\omega_q^2 - \omega^2} \tag{5}$$

where:

$$Z_q = \frac{|q|}{\pi\sqrt{1+F}} \tag{6}$$

and:

$$\omega_q = \overline{v}_F |q| \tag{7}$$

(here $\overline{v}_F = v_F\sqrt{1+F}$). According to [10,12], the complex memory function is given by:

$$M(\omega) \simeq \frac{2\gamma_0}{\pi^2 n m^* \xi \overline{v}_F^3 \sqrt{1+F}} \, \omega + i \, \frac{\gamma_0}{\pi n m^* \overline{v}_F^4 \sqrt{1+F}} \, \omega^2 \equiv b \, \omega + i \, a \, \omega^2 \tag{8}$$

with m^* the band mass, and n the density of the one-dimensional electron gas. In Eq.(8), $p_m \sim \xi^{-1}$ is the maximal possible momentum transfer between two electrons due to the scattering by the impurity potential. When $\xi^{-1} \ll 2p_F$, the impurities do not give rise to backward scattering, and the physics of the scattering is dominated by the forward scattering. In this case, one can approximate the Fourier transform of the factor $C(x)$, by the following form:

$$C(q) = \theta(1 - |q|\xi) \tag{9}$$

where $\theta(x)$ is the step function. Using Eqs.(8) and (4), the frequency-dependent conductivity will be:

$$\sigma(\omega) = Re\ \sigma(\omega) + i\ Im\ \sigma(\omega) \tag{10}$$

with:

$$Re\ \sigma(\omega) = \frac{\overline{D}_c \tau}{1 + (\omega\tau)^2} \tag{11}$$

and:

$$Im\ \sigma(\omega) = \frac{\overline{D}_c}{\omega[1 + (\omega\tau)^2]} \tag{12}$$

Here:

$$\overline{D}_c = \frac{D}{1 + b} \tag{13}$$

is the renormalized charge stiffness, and the time τ is given by:

$$\tau = \frac{a}{1 + b} \tag{14}$$

Due to the restrictions of the model, Eqs.(11) and (12) are valid only for $\omega\tau < 1$. With these results, the complex dielectric function becomes:

$$\epsilon(q, \omega) = 1 - \frac{V(q) q^2 \overline{D}_c}{e^2 \omega^2 (1 + \omega^2 \tau^2)} + i\ \frac{V(q) q^2 \overline{D}_c \tau}{e^2 \omega (1 + \omega^2 \tau^2)} \tag{15}$$

The plasma frequency is determined by the zeros of the dielectric function:

$$\epsilon(q, \omega_p) = 0 \tag{16}$$

With the condition $\omega_p\tau < 1$, Eq.(16) reduces to:

$$e^2\omega_p^2 + iV(q)q^2\overline{D}_c\tau\omega_p - V(q)q^2\overline{D}_c \simeq 0 \tag{17}$$

The stable solution is given by:

$$\omega_p = \frac{V(q)q^2\overline{D}_c\tau}{2e^2}\left[\sqrt{\frac{4e^2}{V(q)q^2\overline{D}_c\tau^2} - 1} - i\right] \tag{18}$$

In the absence of disorder, and in the long-wavelength limit, it was shown [4] that the plasma frequency can be calculated as:

$$\omega_p \sim q\,|\ln(qa)|^{1/2} \tag{19}$$

where $V(q) \sim |\ln(qa)|$ is the Fourier transform of the Coulomb interaction. Here a is a typical confinement width (introduced in order to avoid the logarithmic divergence, typical to Coulomb interaction in a strictly one dimensional system). $Re\ \omega_p$ increases from zero with the increasing of the wavevector q. There is no overdamping for small wavevectors (In two dimensional case [13], and for one dimensional systems in the Born approximation [7], there is an overdamping for small wavevectors). For small wavevectors q, $|Im\ \omega_p|$ is a slightly increasing function. The presence of non-magnetic impurities reduces the electron plasma frequency. A similar behavior was obtained in Ref.[7], in the Born approximation. When the value of the wavevector q increases, $Re\ \omega_p$ becomes of the order of $|Im\ \omega_p|$ and the plasmon mode becomes strongly damped.

3. Analytical results in the Born approximation

In this section, following Ref.[7], we will give an analytical result for the plasmon frequency in the presence of randomly distributed impurities, and in the Born approximation. In this case the Green's function becomes [14]:

$$G(q,\omega)=\frac{1}{\omega-\epsilon(q)+\frac{i}{2\tau}sign(\omega)} \tag{20}$$

where τ is the elastic scattering time. In this case, the polarizability $\Pi(q,\omega)$ is given by:

$$\Pi(q,\omega)=N_0\frac{Dq^2/\tau}{(\omega+i/\tau)\left[\omega-\frac{i}{\tau}\frac{Dq^2/\tau}{(\omega+i/\tau)^2}\right]} \tag{21}$$

Here N_0 is the density of states per spin at the Fermi level, and $D=v_F^2\tau$ is the diffusion coefficient. The Coulomb interaction potential, for $qa\ll 1$, is:

$$V(q)=\frac{2e^2}{\epsilon_0}\,K(|qa|)\simeq-\frac{2e^2}{\epsilon_0}\,\ln|qa| \tag{22}$$

The plasmon frequency is given by the zeros of the dielectric function. In this case, and in the approximation $(\omega_p\tau)^2\ll 1$, the equation for ω_p becomes:

$$1-\frac{f(q)\,(1-i\omega_p\tau)}{Dq^2-i\omega_p-2\omega_p^2\tau}\simeq 0 \tag{23}$$

where:

$$f(q)=\frac{2Dq^2e^2N_0\ln|qa|}{\epsilon_0} \tag{24}$$

In the long-wavelength limit, the solution of Eq.(23) is:

$$\omega_p \simeq \frac{1}{4\tau}\sqrt{8Dq^2\tau - 6\alpha Dq^2\tau \ln|qa| - 1} - i\,\frac{1-\alpha Dq^2\tau \ln|qa|}{4\tau} \tag{25}$$

with

$$\alpha = \frac{2e^2N_0}{\epsilon_0} \tag{26}$$

For wavevectors q between 0 and q_c the plasmon modes are overdamped. Here q_c is a critical wavevector, given by the solution of the following equation:

$$8q^2 - 6\alpha q^2 \ln|qa| - \frac{1}{D\tau} = 0 \tag{27}$$

The critical wavevector is:

$$q_c = \frac{1}{\sqrt{D\tau}}\sqrt{-\frac{1}{3\alpha\, W(-1,-b)}} \tag{28}$$

Here $W(-1,-b)$ is the -1 branch of the Lambert function, and b is given by:

$$b = \frac{a^2}{3\alpha D\tau}\ \exp\left(-\frac{8}{3\alpha}\right) \tag{29}$$

From Eqs.(25) and (28) we will recover, analytically, the conclusions of Sarma and Hwang [7], obtained numerically in the Born approximation. The motivation of such an estimation was pointed in Ref.[7] for the case of high mobility GaAs quantum wire systems, where the localization lengths are very large.

4. Conclusions

We calculated the electron plasma frequency for a quasi-one-dimensional system in the presence of disorder introduced by non-magnetic impurities, taking into consideration of the role of the forward scattering and using the memory function formalism. In this model the presence of non-magnetic impurities reduces the plasma frequency. This result is typical for 1D and 2D systems where the scattering by the impurities strongly affect the plasmon dispersion [7,13]. We also calculate the plasma frequency for an one-dimensional system, in the presence of disorder. We use the Born approximation that describes the scattering of the electrons by the non-magnetic impurities [14]. The analytical result is in agreement with the numerical result of Sarma and Hwang. It was shown that, in the Born approximation, the plasmon modes are overdamped in the long wavelength limit. On the other hand, in our model from Sec.2, there is no overdamping in the $q \to 0$ limit. This is a new result, and this behavior is due to the consideration of the forward scattering in the memory function formalism. However, in such systems, backward scattering are also present, and in pure one-dimensional systems can lead to localization and to a vanishing conductivity for small frequencies. In quasi-one-dimensional systems there can be an interchain coupling that can stabilize a quasimetallic phase. This gives a nonvanishing small frequencies conductivity that could be fitted by a formula given in Ref.[9], and theoretically explained in the model of forward scattering. However, it is difficult to establish an experimental support for the model, because of the experimental difficulties and the narrow interval (in disorder) of the validity of the model.

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